## Large perpendicular magnetic anisotropy in Fe/MgAl<sub>2</sub>O<sub>4</sub> heterostructures

Qingyi Xiang<sup>1,2</sup>, Ruma Mandal<sup>2</sup>, Hiroaki Sukegawa<sup>2</sup>, Yukiko K. Takahashi<sup>2</sup> and Seiji Mitani<sup>1,2</sup> <sup>1</sup>Graduate School of Pure and Applied Sciences, University of Tsukuba, Tsukuba 305-8577, Japan <sup>2</sup>National Institute for Materials Science, Tsukuba 305-0047, Japan

MgAl<sub>2</sub>O<sub>4</sub> is considered a promising alternative barrier material to MgO for magnetic tunnel junctions (MTJs) due to its tunable lattice constant<sup>1)</sup>. The interface-induced perpendicular magnetic anisotropy (PMA) at an MgAl<sub>2</sub>O<sub>4</sub> interface is a crucial property for applications of perpendicularly magnetized MTJs (p-MTJs). Based on a recent theoretical calculation,<sup>2)</sup> the areal PMA energy density of ~1.3 mJ/m<sup>2</sup> was predicted at an Fe/MgAl<sub>2</sub>O<sub>4</sub>(001) interface, which is nearly comparable to that at an Fe/MgO(001) interface (~1.5–1.7 mJ/m<sup>2</sup>). However, a much smaller PMA energy density ~0.4 MJ/m<sup>3</sup>,<sup>3)</sup> comparing with ~1.4 MJ/m<sup>3</sup> in Fe/MgO,<sup>4)</sup> has been experimentally reported in Fe/MgAl<sub>2</sub>O<sub>4</sub>(001) where the MgAl<sub>2</sub>O<sub>4</sub> layers were prepared by post-oxidization of an Mg-Al metallic layer. Therefore, further improvement in the PMA energy of ultrathin-Fe/MgAl<sub>2</sub>O<sub>4</sub>(001) interfaces is expected if a sharp interface is obtained by suppressing atomic intermixing and over-oxidation through process optimization. In this study, we report achievement of large PMA at an Fe/MgAl<sub>2</sub>O<sub>4</sub> by introducing electron-beam deposition of MgAl<sub>2</sub>O<sub>4</sub>.<sup>5)</sup>

Stacks of Cr buffer(30)/Fe(0.7)/MgAl<sub>2</sub>O<sub>4</sub>( $t_{MAO} = 2$  or 3 nm) (unit in nm) multilayers were epitaxially grown

on an monocrystalline MgO(001) substrate by electron-beam evaporation. The Cr and Fe were post-annealed at 800°C and 250°C, respectively. The MgAl<sub>2</sub>O<sub>4</sub>, were post-annealed at various temperatures between 350°C and 500°C to modify the interface conditions. Magnetic properties were investigated using a vibrating sample magnetometer(VSM) and VSM incorporated with superconducting quantum interference device (SQUID). The ultrafast magnetization dynamics property was measured by the time-resolved magneto-optical Kerr effect (TR-MOKE) method.

Figure 1 shows the M-H curve of an optimized Fe (0.7 nm)/MgAl<sub>2</sub>O<sub>4</sub>( $t_{MAO} = 2$  or 3 nm) interface with a large PMA energy up to  $\sim 1.0$  MJ/m<sup>3</sup>, comparable to the reported value for an Fe (0.7 nm)/MgO<sup>4)</sup> (~1.4 MJ/m<sup>3</sup>). We also found that the PMA energy and saturation magnetization  $(M_s)$  were not very sensitive to measurement temperature, where from 100K to 300K, Ki drops from  $\sim 2.0 \text{ mJ/m}^2$  to  $\sim 1.7 \text{ mJ/m}^2$ . The effective damping constant was also evaluated to be ~0.02 by TR-MOKE under high magnetic fields. This study demonstrated robust interface PMA in ultrathin-Fe/MgAl<sub>2</sub>O<sub>4</sub>, which is useful for p-MTJ applications.

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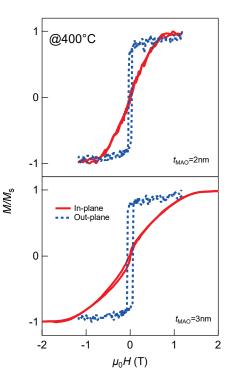


Figure 1 M-H curves for samples annealed at 400°C with  $t_{MAO} = 2$  and 3 nm.

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